



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = 25^\circ\text{C}$
40V	34m Ω @ $V_{GS} = 10\text{V}$	7.2A
	59m Ω @ $V_{GS} = 4.5\text{V}$	5.5A

Description and Applications

This MOSFET has been designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

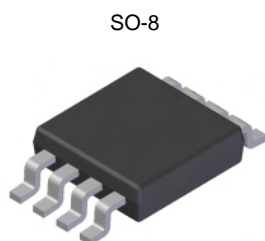
- Motor control
- Backlighting
- DC-DC Converters
- Power management functions

Features and Benefits

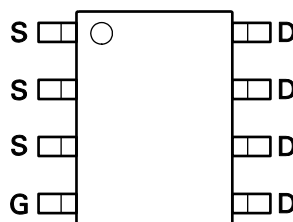
- 100% Unclamped Inductive Switch (UIS) test in production
- Low on-resistance
- Fast switching speed
- Max Q_g rated

Mechanical Data

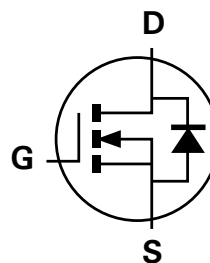
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.074 grams (approximate)



Top View



Top View



Equivalent Circuit

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

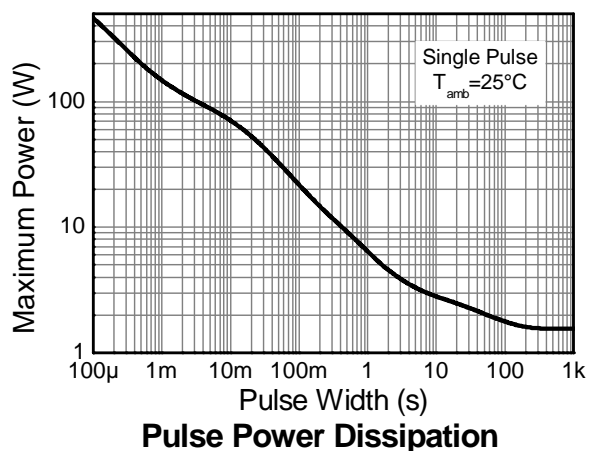
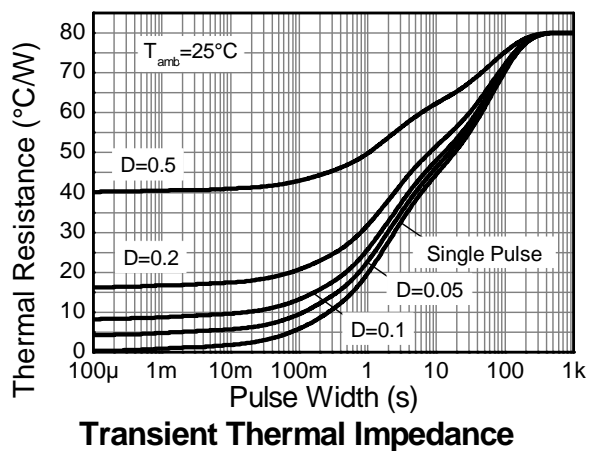
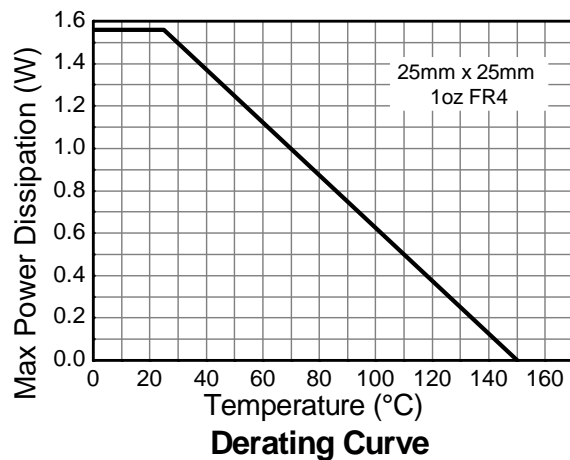
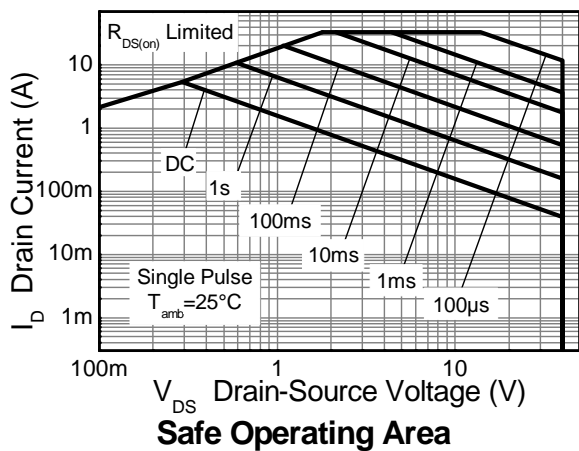
Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	40	V
Gate-Source voltage		(Note 2)	V_{GS}	± 20	V
Single Pulsed Avalanche Energy		(Note 7)	E_{AS}	27	mJ
Single Pulsed Avalanche Current		(Note 7)	I_{AS}	15.25	A
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 4)	I_D	7.2	A
		$T_A = 70^\circ\text{C}$ (Note 4)		5.8	
		(Note 3)		5.4	
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 5)	I_{DM}	33.0	A
Continuous Source current (Body diode)		(Note 4)	I_S	4.1	A
Pulsed Source current (Body diode)		(Note 5)	I_{SM}	33.0	A

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation	(Note 3)	P_D	1.56	W
	Linear derating factor		12.5	
(Note 4)			2.8	
Thermal Resistance, Junction to Ambient	(Note 3)	$R_{\theta JA}$	80	$^\circ\text{C/W}$
	(Note 4)		44.5	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	37	
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

- Notes:
- AEC-Q101 V_{GS} maximum is $\pm 16\text{V}$.
 - For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 - Same as note (3), except the device is measured at $t \leq 10$ sec.
 - Same as note (3), except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.
 - Thermal resistance from junction to solder-point (at the end of the drain lead).
 - UIS in production with $L = 100\mu\text{H}$, $V_{DD} = 40\text{V}$.

Thermal Characteristics

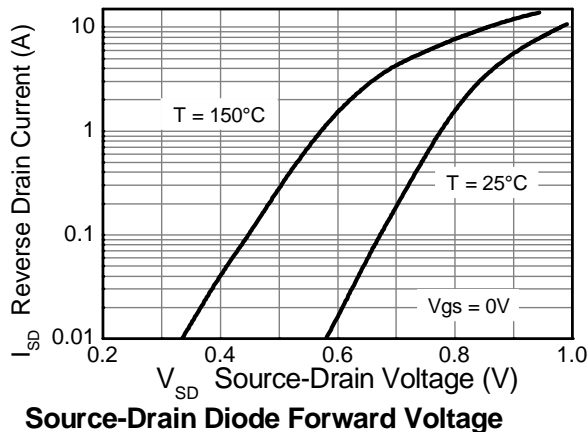
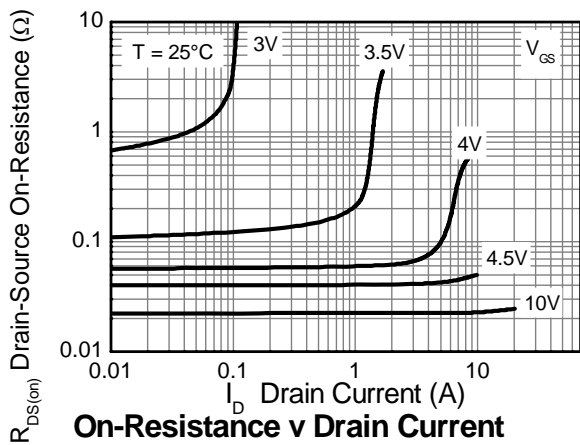
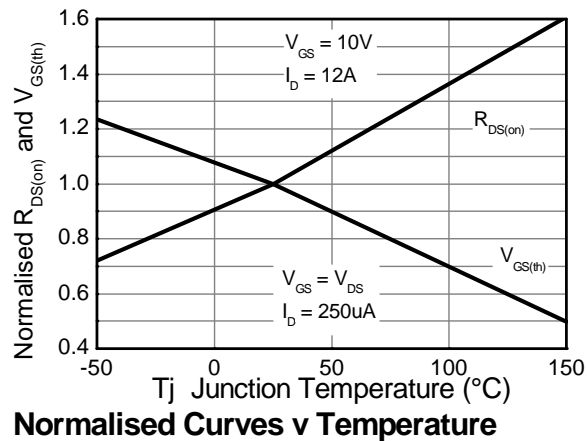
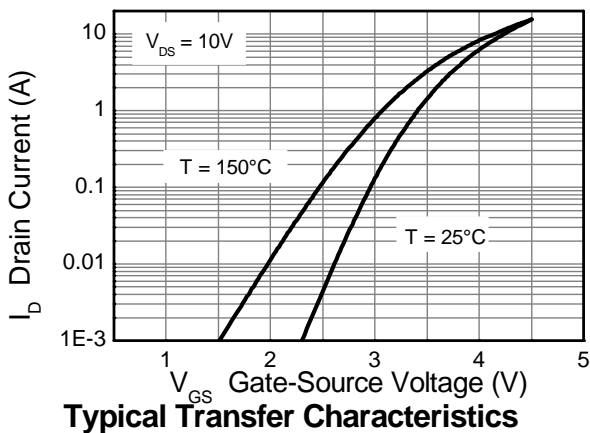
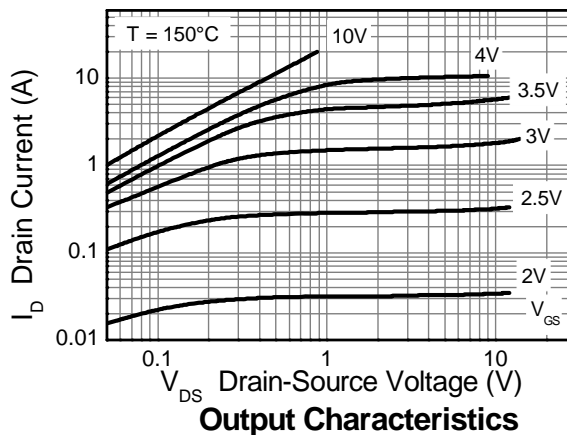
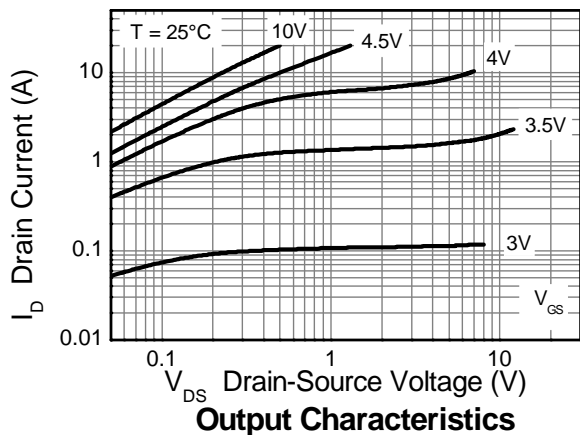


Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

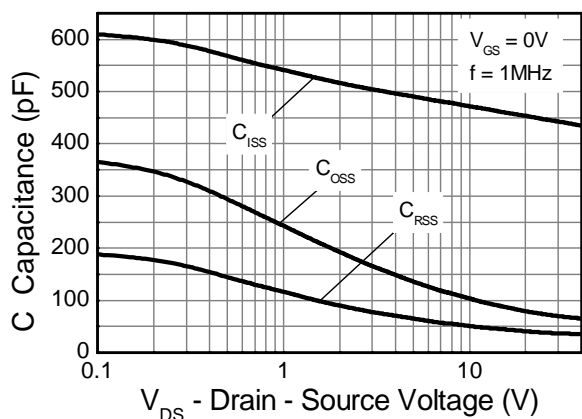
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 40\text{V}$, $V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	$I_D = 250\mu\text{A}$, $V_{DS} = V_{GS}$
Static Drain-Source On-Resistance (Note 8)	$R_{DS(on)}$	—	0.023	0.034	Ω	$V_{GS} = 10\text{V}$, $I_D = 6\text{A}$
			0.039	0.059		$V_{GS} = 4.5\text{V}$, $I_D = 5\text{A}$
Forward Transconductance (Notes 8 & 9)	g_{fs}	—	20.5	—	S	$V_{DS} = 15\text{V}$, $I_D = 6\text{A}$
Diode Forward Voltage (Note 8)	V_{SD}	—	0.87	1.1	V	$I_S = 6\text{A}$, $V_{GS} = 0\text{V}$
Reverse recovery time (Note 9)	t_{rr}	—	11.9	—	ns	$I_S = 2.5\text{A}$, $di/dt = 100\text{A}/\mu\text{s}$
Reverse recovery charge (Note 9)	Q_{rr}	—	4.9	—	nC	
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	453	—	pF	$V_{DS} = 20\text{V}$, $V_{GS} = 0\text{V}$ $f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	79.1	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	40.5	—	pF	
Total Gate Charge (Note 10)	Q_g	—	4.9	8	nC	$V_{GS} = 4.5\text{V}$
Total Gate Charge (Note 10)	Q_g	—	10	18	nC	$V_{GS} = 10\text{V}$
Gate-Source Charge (Note 10)	Q_{gs}	—	1.8	—	nC	
Gate-Drain Charge (Note 10)	Q_{gd}	—	2.4	—	nC	
Turn-On Delay Time (Note 10)	$t_{D(on)}$	—	2.7	—	ns	$V_{DD} = 20\text{V}$, $V_{GS} = 10\text{V}$ $I_D = 1\text{A}$, $R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 10)	t_r	—	2.7	—	ns	
Turn-Off Delay Time (Note 10)	$t_{D(off)}$	—	14	—	ns	
Turn-Off Fall Time (Note 10)	t_f	—	6	—	ns	

- Notes:
8. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$
 9. For design aid only, not subject to production testing.
 10. Switching characteristics are independent of operating junction temperatures.

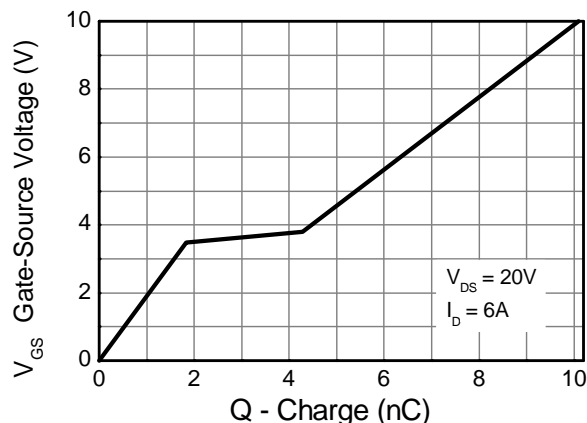
Typical Characteristics



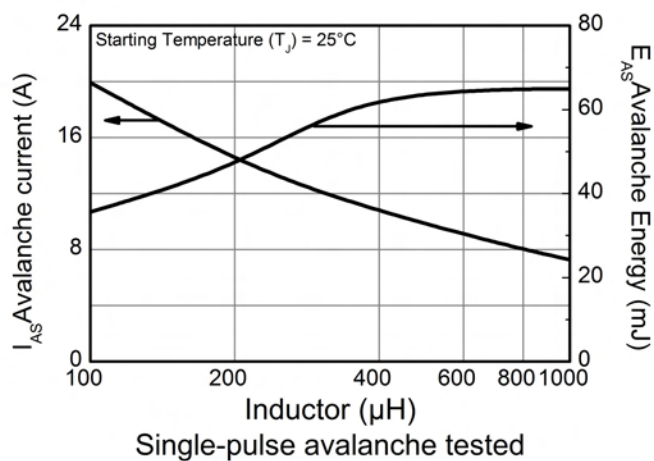
Typical Characteristics – continued



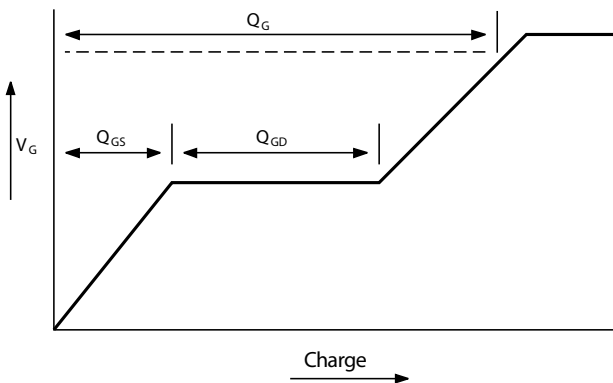
Capacitance v Drain-Source Voltage



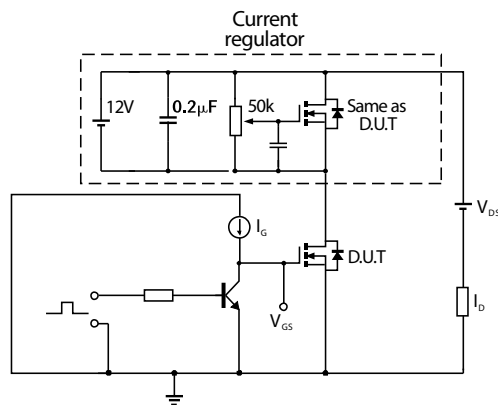
Gate-Source Voltage v Gate Charge



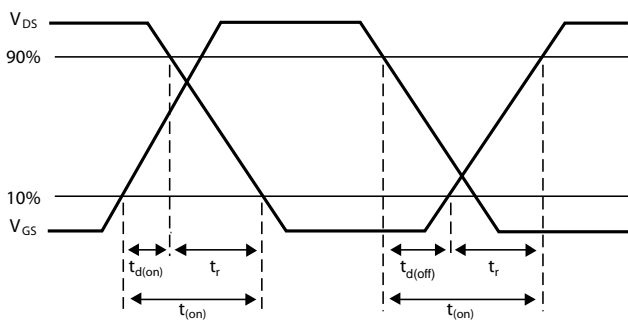
Test Circuits



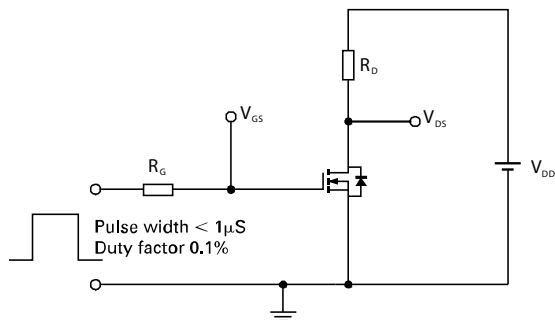
Basic gate charge waveform



Gate charge test circuit

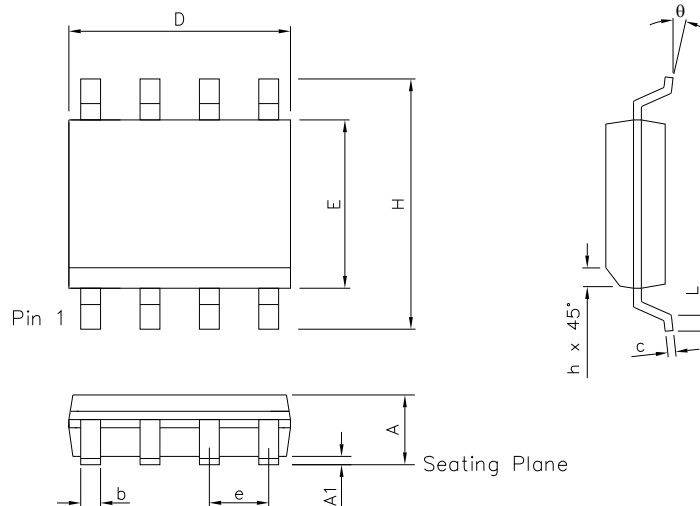


Switching time waveforms



Switching time test circuit

Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.053	0.069	1.35	1.75	e	0.050 BSC		1.27 BSC	
A1	0.004	0.010	0.10	0.25	b	0.013	0.020	0.33	0.51
D	0.189	0.197	4.80	5.00	c	0.008	0.010	0.19	0.25
H	0.228	0.244	5.80	6.20	θ	0°	8°	0°	8°
E	0.150	0.157	3.80	4.00	h	0.010	0.020	0.25	0.50
L	0.016	0.050	0.40	1.27	-	-	-	-	-

Suggested Pad Layout

